

Nanoscale cation motion in TaO_x, HfO_x and TiO_x memristors

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Citation Report

#	ARTICLE	IF	CITATIONS
1	Resistive Switching of Plasma-Treated Zinc Oxide Nanowires for Resistive Random Access Memory. <i>Nanomaterials</i> , 2016, 6, 16.	1.9	25
2	The Resistive Switching Characteristics in ZrO ₂ and Its Filamentary Conduction Behavior. <i>Materials</i> , 2016, 9, 551.	1.3	9
3	Nonlinear thickness and oxidation-dependent transparency and conductance of sputtered titanium suboxide nanofilms. <i>Optical Materials Express</i> , 2016, 6, 1837.	1.6	1
4	Electrochemical processes and device improvement in conductive bridge RAM cells. <i>Physica Status Solidi (A) Applications and Materials Science</i> , 2016, 213, 274-288.	0.8	52
5	Correlation between diode polarization and resistive switching polarity in Pt/TiO ₂ /Pt memristive device. <i>Physica Status Solidi - Rapid Research Letters</i> , 2016, 10, 426-430.	1.2	8
6	Investigation of the behaviour of electronic resistive switching memory based on MoSe ₂ -doped ultralong Se microwires. <i>Applied Physics Letters</i> , 2016, 109, .	1.5	86
7	Nanosculpting of complex oxides by massive ionic transfer. <i>Nanotechnology</i> , 2016, 27, 505703.	1.3	1
8	Interfacial versus filamentary resistive switching in TiO ₂ and HfO ₂ devices. <i>Journal of Vacuum Science and Technology B: Nanotechnology and Microelectronics</i> , 2016, 34, .	0.6	54
9	<i>In situ</i> transmission electron microscopy of resistive switching in thin silicon oxide layers. <i>Resolution and Discovery</i> , 2016, 1, 27-33.	0.9	16
10	On the mechanisms of cation injection in conducting bridge memories: The case of HfO ₂ in contact with noble metal anodes (Au, Cu, Ag). <i>Journal of Applied Physics</i> , 2016, 119, .	1.1	37
11	Integration scheme of nanoscale resistive switching memory using bottom-up processes at room temperature for high-density memory applications. <i>Scientific Reports</i> , 2016, 6, 28966.	1.6	12
12	Memristive behaviour in poly-acrylic acid coated TiO ₂ nanotube arrays. <i>Nanotechnology</i> , 2016, 27, 485208.	1.3	24
13	Glass-Based Transparent Conductive Electrode: Its Application to Visible-to-Ultraviolet Light-Emitting Diodes. <i>ACS Applied Materials & Interfaces</i> , 2016, 8, 35668-35677.	4.0	21
14	Field-enhanced ion transport in solids: Reexamination with molecular dynamics simulations. <i>Physical Review B</i> , 2016, 94, .	1.1	42
15	Impact of oxygen stoichiometry on electroforming and multiple switching modes in TiN/TaO _x /Pt based ReRAM. <i>Applied Physics Letters</i> , 2016, 109, .	1.5	51
16	On the origin of resistive switching volatility in Ni/TiO ₂ /Ni stacks. <i>Journal of Applied Physics</i> , 2016, 120, .	1.1	12
17	Sub-10 nm Ta Channel Responsible for Superior Performance of a HfO ₂ Memristor. <i>Scientific Reports</i> , 2016, 6, 28525.	1.6	177
18	Effect of Oxygen-deficiencies on Resistance Switching in Amorphous YFe _{0.5} Cr _{0.5} O ₃ ~d films. <i>Scientific Reports</i> , 2016, 6, 30335.	1.6	8

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21	Solid-state electrochemistry on the nanometer and atomic scales: the scanning probe microscopy approach. <i>Nanoscale</i> , 2016, 8, 13838-13858.	2.8	27
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28	X-ray spectromicroscopy investigation of soft and hard breakdown in RRAM devices. <i>Nanotechnology</i> , 2016, 27, 345705.	1.3	11
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30	Impact of oxygen exchange reaction at the ohmic interface in Ta ₂ O ₅ -based ReRAM devices. <i>Nanoscale</i> , 2016, 8, 17774-17781.	2.8	116
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